

## AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph [0008] with the following amended paragraph:

In the aforementioned of a method of manufacturing a semiconductor device according to another embodiment of the present invention, the cobalt film is formed to have a thickness of 70Å to 150Å, by keeping a reacting furnace, which initially maintains a pressure of  $1 \times 10^{-7}$  to  $1 \times 10^{-8}$  Torr, in  $1 \times 10^{-2}$  to  $1 \times 10^{-4}$  Torr and at from a ~~normal~~ room temperature to a temperature of 550°C, and by using any one of a DC sputtering method, an RF sputtering method and a CVD method.

Please replace the paragraph [0010] with the following amended paragraph:

In the aforementioned of a method of manufacturing a semiconductor device according to another embodiment of the present invention, the TiN film is formed to have a thickness of 100Å to 500Å, by keeping a reacting furnace, which initially maintains a pressure of  $1 \times 10^{-7}$  to  $1 \times 10^{-8}$  Torr, in  $1 \times 10^2$  to  $1 \times 10^4$  Torr and at from a ~~normal~~ room temperature to a temperature of 400°C, and by using any one of a DC sputtering method, an RF sputtering method and a CVD method.

Please replace the paragraph [0023] with the following amended paragraph:

Referring to Fig. 1B, the insulating film 16 in the area in which the silicide film should be formed is removed. Then, a cobalt film 17 is formed on the whole structure, and a TiN film 18 for preventing abnormal oxidation of the cobalt film 17 is formed thereon. As a result, the cobalt film 17 is formed to be in contact with the poly silicon film 13 and the junction area 15 in the area in which the silicide film should be formed. Here, the cobalt film 17 is formed to have a thickness of 70 to 150Å, by keeping a reacting furnace, which initially maintains a pressure of  $1 \times 10^{-7}$  to  $1 \times 10^{-8}$  Torr, in  $1 \times 10^{-2}$  to  $1 \times 10^{-4}$  Torr and at from a ~~normal~~ room temperature to a temperature of 550°C, and by using any one of a DC sputtering method, an RF sputtering method and a CVD method. On the other hand, a buffer layer for carbon ion implantation should exist for forming a surface amorphous layer of the present invention. Since the TiN film 18 is used as the buffer layer, a thickness of the TiN film 18 is an important factor. At this time, the TiN film 18 is formed to have a thickness of 100 to 500Å, by keeping a reacting furnace, which initially maintains a pressure of  $1 \times 10^{-7}$  to  $1 \times 10^{-8}$  Torr, in  $1 \times 10^2$  to  $1 \times 10^4$  Torr and at from a ~~normal~~ room temperature to a

temperature of 400°C, and by using any one of a DC sputtering method, an RF sputtering method and a CVD method.